

REMARKS

By this amendment, Applicants have amended claim 1 to include the subject matter of the original claim 3 and canceled claim 3, without prejudice. Further, Applicants have amended claim 5 to more accurately reflect the presently claimed invention, amended claims 4 and 10 to correct their dependencies, and amended claim 8 to correct a typographical error. As a result, claims 1-2 and 4-20 are pending in this application. No new matter is believed to be added by these amendments. These amendments are being made to facilitate early allowance of the presently claimed subject matter. Applicants do not acquiesce in the correctness of the objections and rejections and reserves the right to pursue the full scope of the subject matter of the original claims in a subsequent patent application that claims priority to the instant application. Reconsideration in view of the following remarks is respectfully requested.

In the Office Action, claims 1-11 are rejected under 35 U.S.C. § 102(b) as allegedly being anticipated by Japanese Patent No. JP02001168386A (Ito et al.); and claims 12-20 are allowed. Initially, Applicants thank the Examiner for noticing the allowable subject matter of claims 12-20. Applicants respectfully submit that claims 1-2, and 4-11 are allowable for the following reasons.

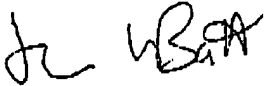
With respect to claim 1, Applicants respectfully submit that Ito et al. fails to disclose a semiconductor structure that includes a substrate, a buffer layer formed on the substrate, a first layer formed above the buffer layer, and a textured nitride layer formed on the first layer. For example, the Office interprets FIG. 8 of Ito et al. as allegedly disclosing a substrate 11, a first layer 31, and a textured nitride layer 35. Based on this interpretation, Applicants respectfully submit that Ito et al. fails to disclose, *inter alia*, the claimed buffer layer and first layer formed above the buffer layer. This configuration enables the textured nitride-based layer to be used for

designs that increase a lifetime and/or a reliability of the semiconductor structure, decrease a noise produced by the semiconductor structure, and/or make the semiconductor structure easier to manufacture. In sharp contrast, Ito et al. merely "eliminate[s] the warpage of the laminate of a substrate and a III nitride compound semiconductor layer." Abstract. As a result, Applicants respectfully request withdrawal of the rejection of claim 1.

With respect to claims 2 and 4-11, Applicants incorporate the same arguments as presented above with respect to claim 1. Further, Applicants respectfully submit that these claims are allowable over the cited art for one or more of their own unique features. For example, claims 4 and 5 comprise an additional layer (claim 4) and structure (claim 5) formed between the buffer layer and the first layer. Additionally, claim 8 comprises a textured nitride layer that partially covers the first layer, and in claim 9, the textured nitride layer forms at least one of: a stripe pattern and a circle pattern. Still further, in claim 10, the first layer and the textured nitride layer comprise a gate barrier structure, and in claim 11, at least one contact is formed on the gate barrier structure. For each of these features of the claimed invention, the Office fails to particularly point out any portion of Ito et al. that allegedly discloses the claimed feature. As a result, Applicants respectfully request withdrawal of each of the rejections of claims 2 and 4-11. In the alternative, should the Office maintain one or more of these rejections, Applicants respectfully request that the Office particularly point out the portion of Ito et al. that allegedly discloses each of the claimed features of claims 4-5 and 8-11.

In light of the above, Applicants respectfully submit that all claims are in condition for allowance. Should the Examiner require anything further to place the application in better condition for allowance, the Examiner is invited to contact Applicants' undersigned representative at the number listed below.

Respectfully submitted,



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